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BT138S-XXE(MS)

Product specification

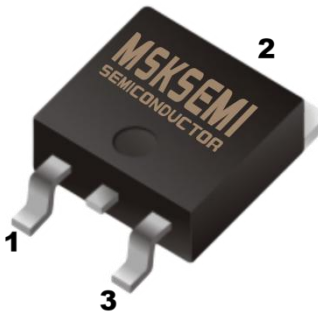
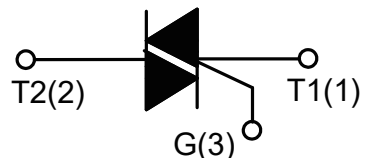


DESCRIPTION

The BT138S-XXE(MS) SCR series with the parallel resistor between Gate and Cathode are especially recommended for use on straight hair, igniter, anion generator, etc.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM} / V_{RRM}	600/800	V

Reference News

PACKAGE OUTLINE	Pin Configuration	Marking	
			
		BT138S-600E(MS)	BT138S-800E(MS)

Notes :XXX represents the order code.

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage($T_j=25^\circ\text{C}$)	V_{DRM}	600/800	V
Repetitive peak reverse voltage($T_j=25^\circ\text{C}$)	V_{RRM}	600/800	V
RMS on-state current($T_C=95^\circ\text{C}$)	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current (full cycle, $F=50\text{Hz}$)	I_{TSM}	95	A
P_t value for fusing ($t_p=10\text{ms}$)	P_t	45	A^2s
Critical rate of rise of on-state current($I_G=2 \times I_{GT}$)	I - II - III	50	$\text{A}/\mu\text{s}$
	IV	10	
Peak gate current	I_{GM}	2	A
Average gate power dissipation	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value	Unit
I_{GT}	$V_D=12V$ $R_L=33\Omega$	I - II-III	MAX	10	mA
		IV		25	
V_{GT}		ALL	MAX	1.5	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=3.3K\Omega$	ALL	MIN	0.2	V
I_L	$I_G=1.2I_{GT}$	I - III	MAX	30	mA
		II- IV		40	
I_H	$I_r=100\text{mA}$		MAX	25	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$		MIN	50	V/ μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=15\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.6	V
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	μA
I_{RRM}		$T_j=125^\circ\text{C}$	1	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case(AC)	1.7	$^\circ\text{C/W}$
$R_{th(j-a)}$	junction to ambient	70	$^\circ\text{C/W}$

FIG.1: Maximum power dissipation versus RMS on-state current

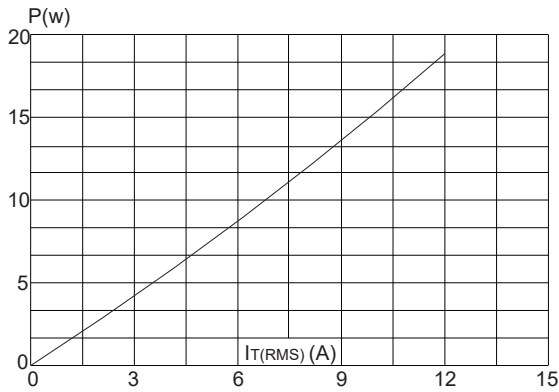


FIG.3: Surge peak on-state current versus number of cycles

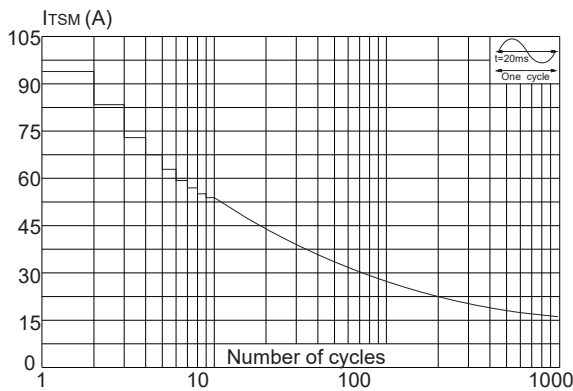


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t (I - II -III: $dI/dt < 50\text{A}/\mu\text{s}$; IV: $dI/dt < 10\text{A}/\mu\text{s}$)

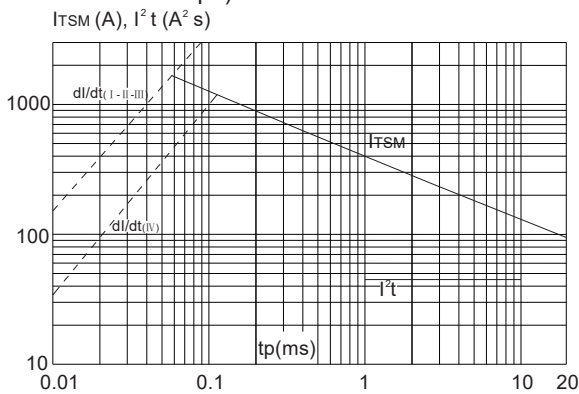


FIG.7: Relative variations of holding current versus junction temperature

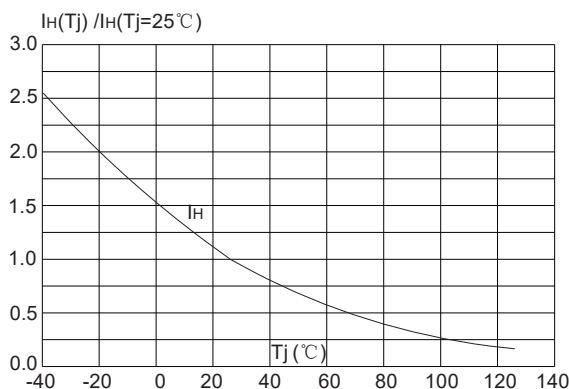


FIG.2: RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness: $35\mu\text{m}$)(full cycle)

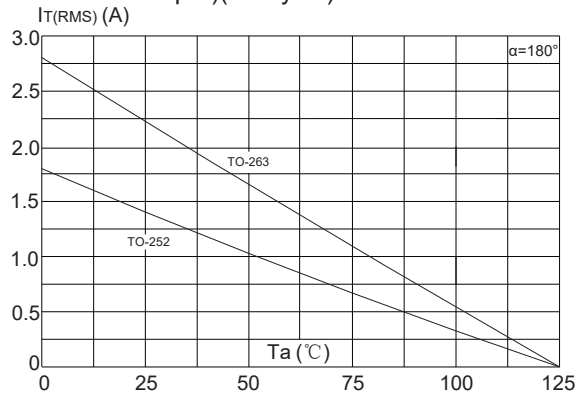


FIG.4: On-state characteristics (maximum values)

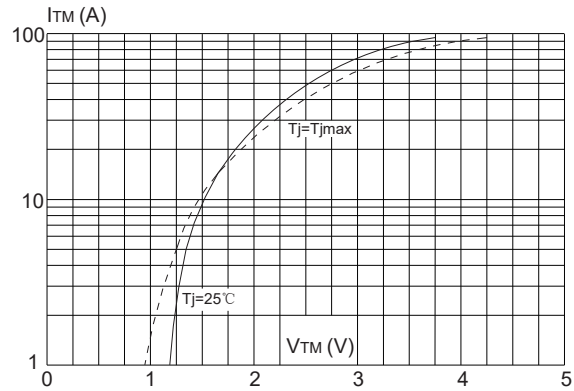


FIG.6: Relative variations of gate trigger current versus junction temperature

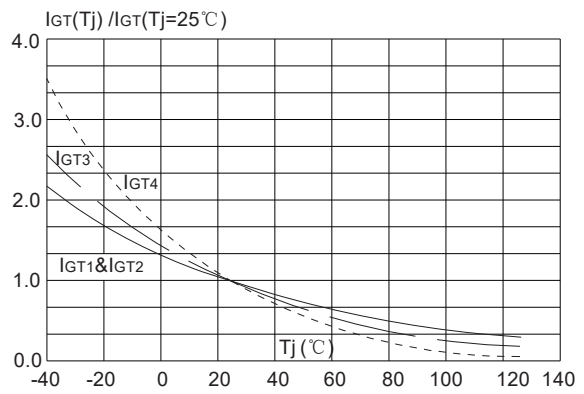
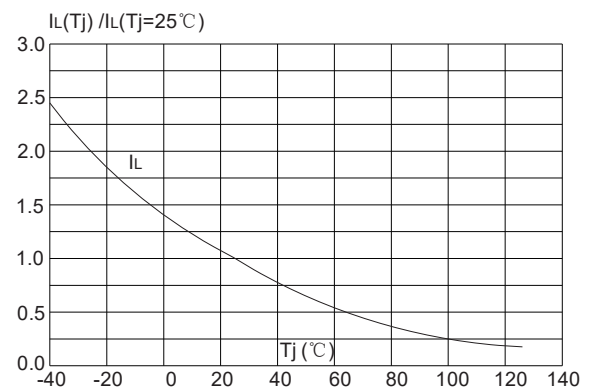
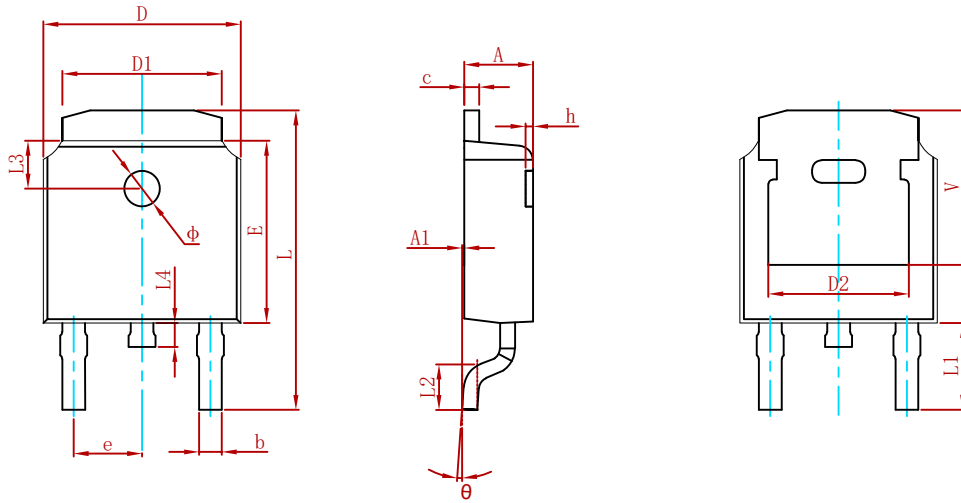


FIG.8: Relative variations of latching current versus junction temperature

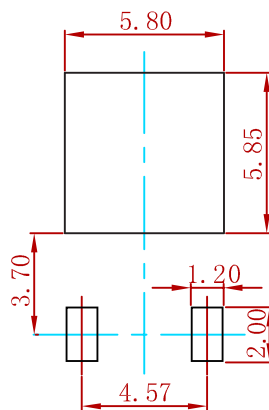


PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	

Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05mm.
3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
BT138S-XXE(MS)	TO-252	2500

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